

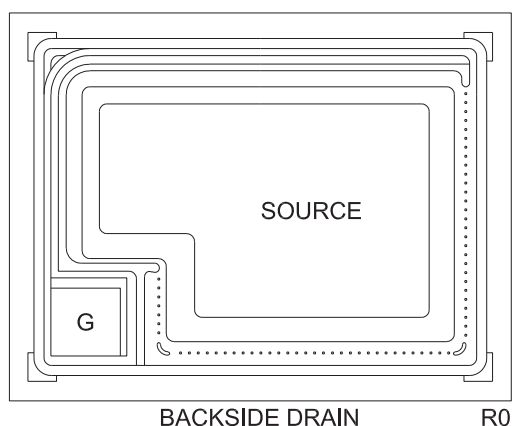
PROCESS CP357X
Small Signal MOSFET Transistor
N-Channel Enhancement-Mode MOSFET Chip



PROCESS DETAILS

Die Size	22 x 17 MILS
Die Thickness	5.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	14 x 9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER

63,570

PRINCIPAL DEVICE TYPE

CMLDM3737

R0 (17-November 2010)

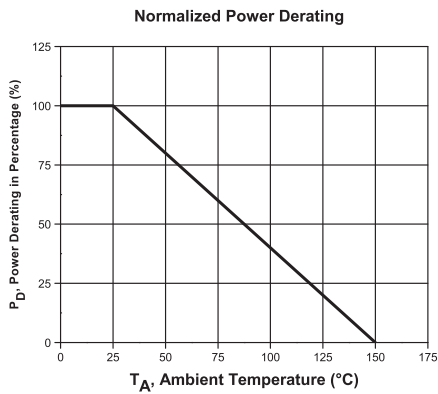
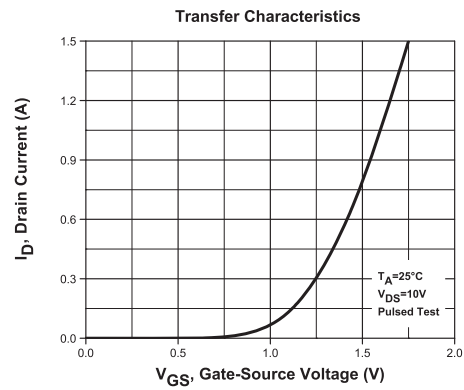
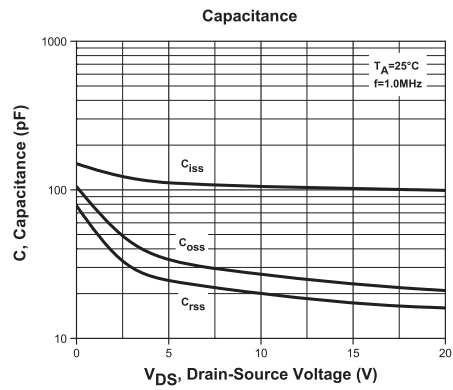
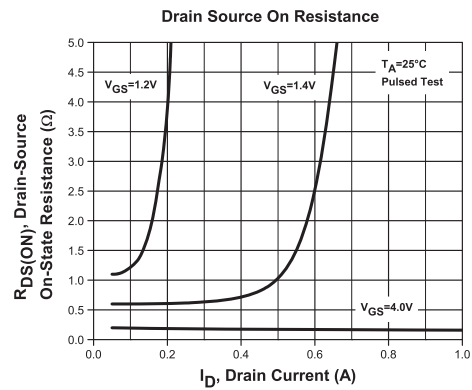
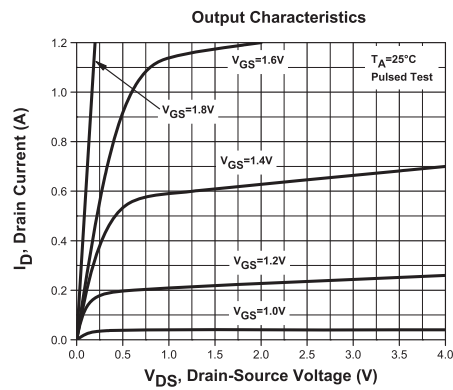
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PROCESS CP357X

Typical Electrical Characteristics



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